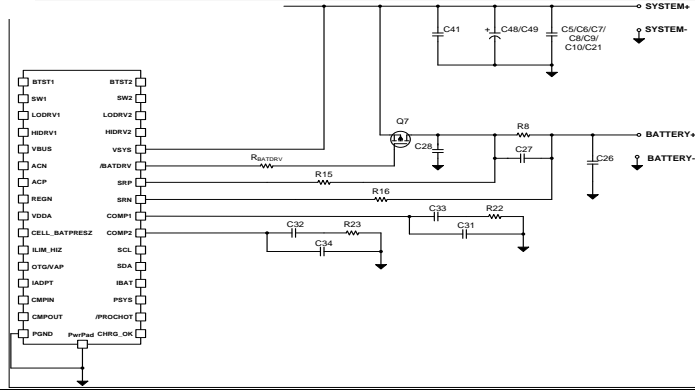


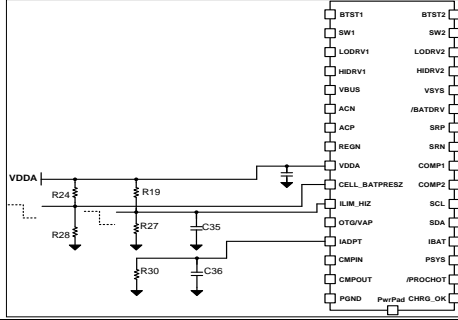
INPUT POWER - DESIGN CHECKLIST							
PIN NAME	REQUIREMENT	COMPONENT	MIN	TYP	MAX	DESCRIPTION	COMMENTS AND RELEVANT EQUATIONS
ADAPTER / ADAPTER	Required	C3+C4+C23+C24+C44+C45	30 uF	60 uF		Forward Mode: Ceramic high frequency filtering input capacitors. Reverse Mode: Converter ceramic output filtering capacitors.	Input source to the charger For a 45 W to 65 W 5% load, use at least (4x) 10 uF capacitors with an extra (2x) 10 uF DNP. For a 65 W to 90 W 5% load, use at least (6x) 10 uF capacitors with an extra (2x) 10 uF DNP. Refer to "Table 10-1. Minimum Input Capacitance Requirement" and "10.2.2.3 Input Capacitor" sections of BQ25720 datasheet for more information.
	Required	C33	33 uF			Forward Mode: Tantalum polymer high frequency filtering input capacitor. Reverse Mode: Converter tantalum polymer output filter capacitor.	For > 90W 5% loads, with a 45 or 55(BQ2573x) battery configuration, use at least (1x) 33 uF tantalum polymer capacitor. Refer to "Table 10-1. Minimum Input Capacitance Requirement" and "10.2.2.3 Input Capacitor" sections of BQ25720 datasheet for more information.
	Recommended DNP	R3, R4	3.9 Ohm			Input hot-plug snubber circuit	For systems with high input cable or trace inductance and hot plug use cases, add experimentally derived RC snubber to limit inrush current and input voltage overshoot. R3 and R4 in parallel should be sized appropriately to handle the inrush current. $R3  R4 = \frac{1}{2f} \frac{I_{inrush,max}}{C_{input}}, \text{ where } 0 < f_{\text{switching}} < 1$
	Optional	C18	1 uF			Input protection turn-on/turn-off delay	$C_{18,min} = \frac{I_{inrush,max}}{\sqrt{V_{input} + \Delta V_{overshoot,max}} \cdot \omega_{input,resonant}} + \frac{1}{2f_{\text{switching}}}, \text{ where } \omega_{input,resonant} = \frac{1}{2L_{\text{input}}C_{input}}$
	Optional	Q5, Q6				Back-to-Back input protection FETs, MOSFETs	Size to clamp maximum allowable VGS for Q5 and Q6.
	Optional	R9				Input protection turn-on/turn-off delay	Size Q5 and Q6 appropriately to handle input power, optimize losses, and allow for smooth turn-on and turn-off.
	Optional	C22				Input protection turn-on/turn-off control	Select delay and control circuits to avoid conflicts with charging timing.
	Optional	Q9, Q10, Q11, Q12, Q13				Input protection turn-on/turn-off control	Note: If the Q5- and Q6 input protection circuit and is to function correctly, R13 (see VBUS) must be connected to the Drain of Q5.
	Optional	Z1				Input protection gate-source Zener clamp diode	
	ACP-ACN	3-2	Required	R2 (R <sub>AC</sub> )	5 mOhm	20 mOhm	Input current sensing resistor. This is used for both input current limit regulation and for inductor current sensing of the average current mode control architecture of the charger.
Recommended		R11, R12	4.99 Ohm			Input current sense switching noise and common mode noise filtering	Select R11 / C46 and R12 / C47 such that the filter time constant is between 47 ns and 200 ns
Recommended		C46, C47	33 nF			High frequency switching current spike filtering	Note: Too high of a capacitance on this side of RAC could impact the converter stability. This is the reason for limiting the maximum capacitance to 20nF.
Recommended		C17	1 uF	20 nF	20 nF	Differential mode noise filtering	
Recommended DNP		C11	6.01 uF			Differential mode noise filtering	
VBUS	1	Required	C25	0.47 uF	0.47 uF	Input voltage noise decoupling capacitor	IC input voltage rail Placed close to the IC VBUS pin. K78 capacitor is recommended.
	Recommended	R13	1 Ohm			Input voltage rail inrush current limiting	Size appropriately to handle large input overshoots and current spikes.
REGN	28	Required	C30	2.2 uF	2.2 uF	Internal LDO output stabilizing capacitor	Internal LDO output Placed close to the IC REGN pin. K78 capacitor is recommended.
	Recommended	R18	10 Ohm			Current limit sense resistor	Internal reference bias Placed close to the IC VDDA pin. K78 capacitor is recommended.
HDRV1	31	Required	Q1			Converter (Forward Buck Mode) active High-Side N-Channel MOSFET	Converter (Forward Buck Mode) High-Side N-Channel MOSFET gate driver This is also the reverse boost mode synchronous High-Side MOSFET. Refer to "Typical Application" section of the datasheet for more details on the Power Stage MOSFET selection criterion.
	Recommended	R <sub>DS(on)1</sub>	0 Ohm			Q1 High-Side MOSFET gate drive strength limiting resistor	For non-ideal layouts with EMI constraints, add an experimentally derived resistance to slow down the Q1 turn-on and turn-off.
	Recommended	C19	150 pF			Low-Side MOSFET Gate-Source holding capacitor	Stand to increase the effective C <sub>gs</sub> in comparison to the C <sub>gd</sub> of Q2. This helps prevent the Miller capacitance from driving the MOSFET gate during a high dV/dt event. This is more important when Q <sub>gs</sub> and Q <sub>gd</sub> of Q2 are similar in magnitude.
LODRV1	29	Required	Q2			Converter (Forward Buck Mode) synchronous Low-Side N-Channel MOSFET	Converter (Forward Buck Mode) Low-Side N-Channel MOSFET gate driver This is also the reverse boost mode active Low-Side MOSFET. Refer to "Typical Application" section of the datasheet for more details on the Power Stage MOSFET selection criterion.
	Recommended	R <sub>DS(on)2</sub>	0 Ohm			Q2 Low-Side MOSFET gate drive strength limiting resistor	For non-ideal layouts with EMI constraints, add an experimentally derived resistance to slow down the Q2 turn-on and turn-off.
	Recommended	C19	150 pF			Low-Side MOSFET Gate-Source holding capacitor	Stand to increase the effective C <sub>gs</sub> in comparison to the C <sub>gd</sub> of Q2. This helps prevent the Miller capacitance from driving the MOSFET gate during a high dV/dt event. This is more important when Q <sub>gs</sub> and Q <sub>gd</sub> of Q2 are similar in magnitude.
SW1-SW2, BTST1, BTST2	32-23, 30, 35	Required				Converter inductor	Buck-boost switching nodes and High-Side MOSFET bootstrap network SW1 and SW2 should be connected to minimize the inductive path from the IC pin to the inductor, L1. Refer to EVM.
	Recommended	C15	47 nF			Converter bootstrap capacitor for Q1 High-Side N-Channel MOSFET gate driver	
	Recommended	R <sub>DS(on)1</sub>	0 Ohm			Bootstrap capacitor discharge current limiting resistor	For non-ideal layouts with EMI constraints, add an experimentally derived resistance to slow down the Q1 turn-on.
	Recommended	C16	47 nF			Converter bootstrap capacitor for Q4 High-Side N-Channel MOSFET gate driver	
HDRV2	24	Required	Q4			Converter (Forward Boost Mode) synchronous High-Side N-Channel MOSFET	Converter (Forward Boost Mode) High-Side N-Channel MOSFET gate driver This is also the reverse boost mode High-Side MOSFET. Refer to "Typical Application" section of the datasheet for more details on the Power Stage MOSFET selection criterion.
	Recommended	R <sub>DS(on)2</sub>	0 Ohm			Q4 High-Side MOSFET gate drive strength limiting resistor	For non-ideal layouts with EMI constraints, add an experimentally derived resistance to slow down the Q4 turn-on and turn-off.
	Recommended	C19	150 pF			Low-Side MOSFET Gate-Source holding capacitor	Stand to increase the effective C <sub>gs</sub> in comparison to the C <sub>gd</sub> of Q3. This helps prevent the Miller capacitance from driving the MOSFET gate during a high dV/dt event. This is more important when Q <sub>gs</sub> and Q <sub>gd</sub> of Q3 are similar in magnitude.
LODRV2	26	Required	Q3			Converter (Forward Boost Mode) active Low-Side N-Channel MOSFET	Converter (Forward Boost Mode) Low-Side N-Channel MOSFET gate driver This is also the reverse boost mode Low-Side MOSFET. Refer to "Typical Application" section of the datasheet for more details on the Power Stage MOSFET selection criterion.
	Recommended	R <sub>DS(on)2</sub>	0 Ohm			Q3 Low-Side MOSFET gate drive strength limiting resistor	For non-ideal layouts with EMI constraints, add an experimentally derived resistance to slow down the Q3 turn-on and turn-off.
	Recommended	C19	150 pF			Low-Side MOSFET Gate-Source holding capacitor	Stand to increase the effective C <sub>gs</sub> in comparison to the C <sub>gd</sub> of Q3. This helps prevent the Miller capacitance from driving the MOSFET gate during a high dV/dt event. This is more important when Q <sub>gs</sub> and Q <sub>gd</sub> of Q3 are similar in magnitude.

BQ2570X, BQ2571X, BQ2572X, BQ2573X (aside from BQ25731) - Output Power Design



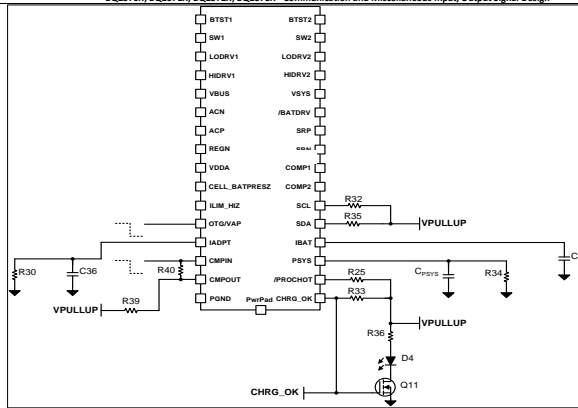
OUTPUT POWER - DESIGN CHECKLIST						COMMENTS AND RELEVANT EQUATIONS	
PIN NAME	REQUIREMENT	COMPONENT	MIN	TYP	MAX	DESCRIPTION	
<b>System output either from converter regulation of input source or battery</b>							
SYSTEM+ / SYSTEM-	Required	C3+C6+C7+C8+C9+CLD+C21 (Ctotal)	70 uF	90 uF		<b>Forward Mode:</b> Converter ceramic output filtering capacitors. <b>Reverse Mode:</b> Ceramic high frequency filtering input capacitors.	For a 45 W to 65 W SYS load, use at least (7x) 10 uF capacitors with an extra (2x) 10 uF DNP. For a 65 W to 90 W SYS load, use at least (8x) 10 uF capacitors with an extra (2x) 10 uF DNP. K78 capacitors are recommended. Refer to "Table 10-2. Minimum Output Capacitance Requirement" and "10.2.2.4 Output Capacitor" sections of BQ25720 datasheet for more information.
	Required	C48+C49 (Ctotal)	33 uF	66 uF		<b>Forward Mode:</b> Converter tantalum polymer output filtering capacitors. <b>Reverse Mode:</b> Tantalum polymer high frequency filtering input capacitor.	For > 65W SYS loads, with a 45 or 55(BQ2573x) battery configuration, use at least (1x) 33 uF tantalum polymer capacitor. For > 90W SYS loads, with a 45 or 55(BQ2573x) battery configuration, use at least (2x) 33 uF tantalum polymer capacitors. Refer to "Table 10-2. Minimum Output Capacitance Requirement" and "10.2.2.4 Output Capacitor" sections of BQ25720 datasheet for more information.
VSYS	Required	-	-	-	-	-	<b>System output regulation sensing point</b> VSYS must be Kelvin connected to the output filter stage connected to SYSTEM+. The connection should be tied as close to the output resonant filter portion of the system rail (C <sub>total</sub> ) as possible. Take precaution to not Kelvin connect this pin significantly far away from the output filter and/or IC VSYS pin, such that a large IR loss from the system load is sensed by VSYS.
	Recommended	C41		10 nF		Noise decoupling capacitor	Place close to the IC VSYS pin.
BATTERY+ / BATTERY-	Required	C26	20 uF	Refer to device EVM		Charge current regulation stability and filtering capacitor	<b>Battery or battery pack connection to the charger</b> Connected to the SRN pin, this capacitor is critical for accurate battery voltage sensing. From the SRN pin, the Constant Voltage (CV) phase of charging will regulate the voltage to the MaxCharge(Voltage) Register setting. When charging is disabled and the SRN voltage is above the MinSys(Voltage) Register setting, the sensed voltage on the SRN pin is also used as a reference to regulate the VSYS voltage such that: $V_{SYS} = V_{SRN} \times V_{SRN} + 100 \text{ mV} / 150 \text{ mV}$ (other than BQ25731). K78 capacitor is recommended.
	Required	R8 (R <sub>ch</sub> )	5mΩ	10 mΩ	20 mΩ	Charge current sensing resistor	<b>Differential charge current sensing</b> Sense resistor range depends on device. For BQ2570x and BQ2571x, the range is 10 mΩ/20 mΩ. For BQ2572x and BQ2573x, the range is 5 mΩ/10 mΩ. This will impact the IBAT and PPS1 pin measurements. In Charge Current regulation for the Constant Current (CC) phase of charging, the CHG current is regulated as a differential voltage across R <sub>ch</sub> such that: $I_{CHG} = \frac{V_{SRN} - V_{SRN}}{R_{ch}} \times \text{ChargeCurrent}$ Register setting. If the charger is either in INDFM, VINDFM, or other protections, the regulated charge current may be lower than the programmed value.
SRP-SRN	Required	C28	1 uF	1 uF		Noise filter capacitor	
	Recommended	C27		0.1 uF		Differential mode noise filtering	
	Recommended	R15, R16		10 Ω	10 Ω	Battery reverse polarity protection resistors	Stand with a low power rating such that in the event of a reverse polarity event with the battery pack, the resulting unintended current flow will damage R15 or R16 first rather than the charger or the system. This acts as a crude form of reverse polarity protection.
/BATDRV	Required	Q7		-		External battery to system power path P-Channel MOSFET (BAT111)	<b>External battery MOSFET driver</b>
	Recommended	Ractdrv		0 Ω		CC gate drive strength limiting resistor.	
COMP1, COMP2	Required	C33				Average current control outer loop compensation network	Place close to the IC COMP1 pin.
	Required	C32				Average current control outer loop high frequency filtering capacitor	Ideally connect the ground return of these components to a signal ground, rather than a power ground. If not possible, connect the ground return as close to the IC PGND pin as possible.
	Required	C31				Average current control inner loop compensation network	Place close to the IC COMP2 pin.
	Required	R23				Average current control inner loop compensation network	Ideally connect the ground return of these components to a signal ground, rather than a power ground. If not possible, connect the ground return as close to the IC PGND pin as possible.
	Required	C34				Average current control inner loop high frequency filtering capacitor	

BQ2570X, BQ2571X, BQ2572X, BQ2573X - Hardware Programmed Input Design



HARDWARE PROGRAMMED INPUT - DESIGN CHECKLIST							
PIN	REQUIREMENT	COMPONENT	MIN	TYP	MAX	DESCRIPTION	COMMENTS AND RELEVANT EQUATIONS
CELL_BATPRESZ	Required	R24		*kΩ		Resistor divider network referenced to the VDDA rail to set the default charging voltage, default minimum system voltage, and maximum system voltage. Also input to signal charger of a battery absence.	Default charging and system parameter setting The CELL_BATPRESZ cell count settings is determined once VDDA is powered, typically after a valid input source is applied. If CELL_BATPRESZ is pulled LOW externally, this indicates to the charger that the battery has been removed. This will reset the ChargeCurrents register setting to 0mA. If enabled in the ProchotOption() Register setting, this will also trigger the ProchotStatus() register flag.
		R28		*kΩ			
ILM_HIZ	Required	R19		*kΩ		Resistor divider network to set an external input current limit.	External input current limit setting and converter high impedance control The voltage set at this pin through the resistor divider network determines the externally set input current limit setting.
		R27		*kΩ			
	Recommended CNP	C35		*μF		Noise decoupling capacitor	Place close to the ILM_HIZ pin.
IADPT	Required	R30	-3%	*Ω	+3%	Resistor used to indicate inductor selection and output an analog input current measurement	Inductor selection setting and input current measurement output Place close to the IADPT pin.
		C36		100 pF		Noise decoupling capacitor	

BQ2570X, BQ2571X, BQ2572X, BQ2573X - Communication and Miscellaneous Input/Output Signal Design



COMMUNICATION AND MISC INPUT/OUTPUT SIGNAL - DESIGN CHECKLIST						COMMENTS AND RELEVANT EQUATIONS	
PIN NAME	REQUIREMENT	COMPONENT	MIN	TYP	MAX	DESCRIPTION	
OTG/VAP/FRS	5	Optional	-	-	-	OTG, VAP, or FRS mode	OTG, VAP, FRS mode enable Pull HIGH to enable different mode. Refer to datasheet for details.
IADPT	8	Required	R30	3%	10	+3%	Inductor selection setting and analog calculated input current measurement output The IADPT_GAIN setting is programmable in the ChargeOption0() Register. Resistor used to indicate inductor selection and output an analog input current measurement
		Recommended	C36	100			Noise decoupling capacitor Place close to the IC IADPT pin.
CMPIN, CMPOUT	14, 15	Optional	R39, R40	10			Independent comparator input and output Pullup resistor for CMPOUT open-drain output Refer to datasheet and EVM
SCL, SDA	13, 12	Required	R32, R35	10			I2C or SMBus Open-drain communication input and output I2C or SMBus communication is required for charging to operate on this device as intended. This is a host controlled charging buck-boost controller. Charging is not autonomous without host intervention. Pullup resistors for the open-drain I2C or SMBus clock and data communication bus
IBAT	9	Optional	C37	100			Analog battery current measurement output Place close to the IC IBAT pin. The IBAT_GAIN setting is programmable in the ChargeOption0() Register. Analog voltage output representing the battery charge or discharge current measurement
PSYS	10	Optional	R34	30.1			Analog system power measurement output Analog current output representing the system power, measured as a voltage across R34. Noise decoupling capacitor Place close to the IC PSYS pin.
/PROCHOT	11	Optional	R25	10			Active LOW open-drain output signal for Processor Hot flags Pullup resistor for /PROCHOT open-drain output
CHRG_OK	4	Optional	R33				Active HIGH open-drain output signal of input source status Pullup resistor for CHRG_OK open-drain output Open drain active high indicator to inform the system good power source is connected to the charger input. Connect to the pullup rail via 10 kΩ resistor.
		Optional	R36, D4, Q11				CHRG_OK LED indication control
PwrPad	-	Required	-	-	-	-	IC Thermal dissipation pad Main point of heat dissipation for the IC Connect to a large Power Ground plane(s) and/or layer(s) with at least 5-point via connections